

Description

The SI4420DYPBF uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Battery protection or in other Switching application.



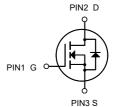
General Features

 $V_{DS} = 30V I_{D} = 18A$

 $R_{DS(ON)}$ < 6.5m Ω @ V_{GS} =10V

 $R_{DS(ON)} < 12m\Omega$ @ $V_{GS}=4.5V$





Application

Battery protection

Load switch

Uninterruptible power supply

N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
1 Toddet ID	1 dek	Brand	Giy(i OO)
SI4420DYPBF	SOP-8(SO-8)	HXY MOSFET	3000

Absolute Maximum Ratings (T_C=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
V _{DS}	Drain-Source Voltage	30	V	
V _G s	Gate-Source Voltage	±20	V	
I _D	Drain Current-Continuous	18	А	
I _D (70 °C)	Drain Current-Continuous(T _C =70 °C)	8.2	Α	
Ідм	Pulsed Drain Current	42	Α	
P _D	Maximum Power Dissipation	1.5	W	
T _J ,T _{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}\!$	
Rejc	Thermal Resistance,Junction-to-Case ^(Note 2)	36	°C/W	

N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V	
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25°C , I _D =1mA		0.027		V/°C	
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =10A		5.5	6.5	· mΩ	
	Static Dialii-Source On-Resistance	V _{GS} =4.5V , I _D =8A		9	12		
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.5	2.5	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	VGS=VDS , ID =250UA		-5.8		mV/°C	
1	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =25°C			1		
I _{DSS}		V _{DS} =24V , V _{GS} =0V , T _J =55°C			5	uA	
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA	
gfs	Forward Transconductance	V _{DS} =5V , I _D =10A		5.8		S	
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		2.2	3.8	Ω	
Qg	Total Gate Charge (4.5V)			12.6	17.6		
Qgs	Gate-Source Charge	V _{DS} =15V , V _{GS} =4.5V , I _D =10A		4.2	5.9	nC	
Q _{gd}	Gate-Drain Charge			5.1	7.1		
T _{d(on)}	Turn-On Delay Time			6.2	12.4		
Tr	Rise Time	V_{DD} =15V , V_{GS} =10V , R_{G} =3.3 Ω		59	106	ns	
$T_{d(off)}$	Turn-Off Delay Time	I _D =10A		27.6	55		
T _f	Fall Time			8.4	16.8		
Ciss	Input Capacitance			1317	1845		
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		163	228.2	pF	
Crss	Reverse Transfer Capacitance			131	183.4		
ls	Continuous Source Current ^{1,5}	V V 0V 5 0			10.3	Α	
I _{SM}	Pulsed Source Current ^{2,5}	V _G =V _D =0V , Force Current			42	Α	
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1.2	V	
t _{rr}	Reverse Recovery Time			12.5		nS	
Q _{rr}	Reverse Recovery Charge	lF=10A , dl/dt=100A/μs , T _J =25°C		5		nC	

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\,\leq\,300\text{us}$, duty cycle $\,\leq\,2\%$
- 3. The EAS data shows Max. rating . The test condition is V_{DD} =25V, V_{GS} =10V,L=0.1mH, I_{AS} =35A
- 4.The power dissipation is limited by 150°C junction temperature
- 5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics

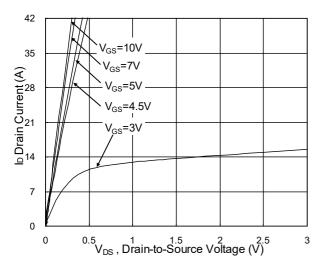


Fig.1 Typical Output Characteristics

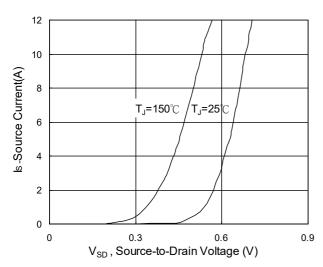


Fig.3 Forward Characteristics of reverse

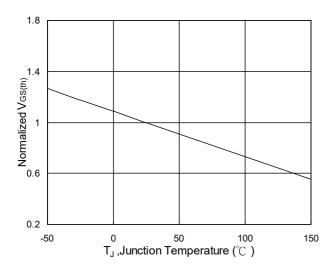


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

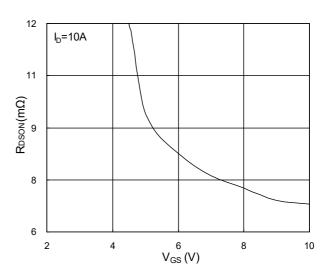


Fig.2 On-Resistance vs. Gate-Source

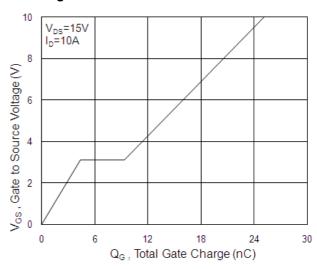


Fig.4 Gate-Charge Characteristics

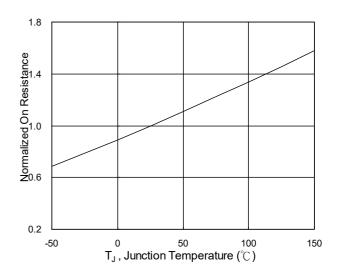
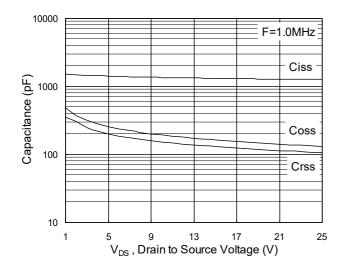


Fig.6 Normalized R_{DSON} vs. T_J





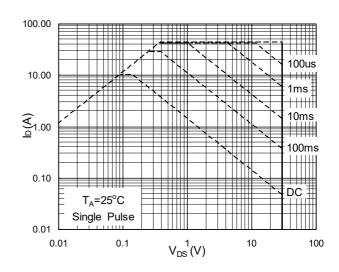


Fig.7 Capacitance

Fig.8 Safe Operating Area

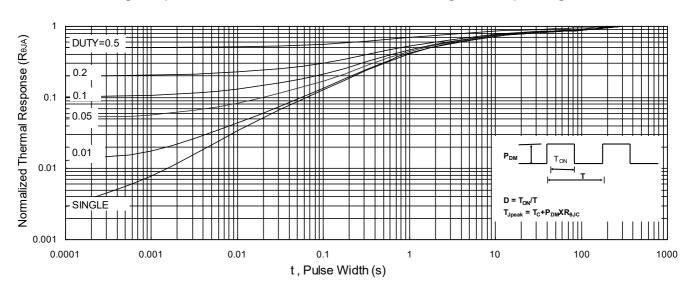


Fig.9 Normalized Maximum Transient Thermal Impedance

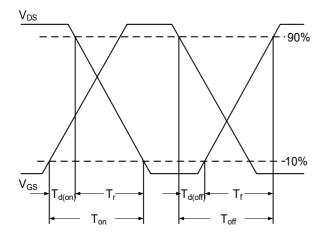


Fig.10 Switching Time Waveform

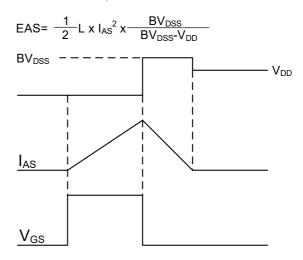
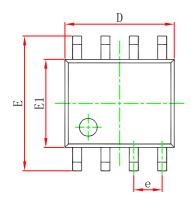
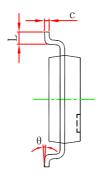
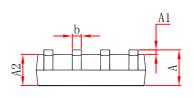


Fig.11 Unclamped Inductive Switching Waveform

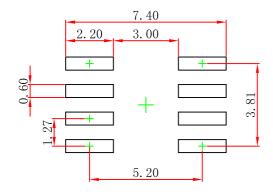
SOP-8(SO-8) Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
3y111001	Min	Max	Min	Max	
A	1. 350	1.750	0.053	0.069	
A1	0.100	0. 250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
c	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0. 197	
e	1. 270 (BSC)	0.050 (BSC)		
E	5.800	6.200	0. 228	0. 244	
E1	3.800	4.000	0.150	0. 157	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



- Note:
 1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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